74LVC1G58-Q100

Low-power configurable multiple function gate

Rev. 1 — 10 June 2014 Product data sheet

1. General description

The 74LVC1G58-Q100 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XOR, inverter and buffer. All inputs can be connected to V_{CC} or GND.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

All inputs (A, B and C) are Schmitt trigger inputs. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- ±24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G58GW-Q100	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC1G58GV-Q100	–40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 2. Marking

Type number	Marking code[1]
74LVC1G58GW-Q100	YK
74LVC1G58GV-Q100	V58

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

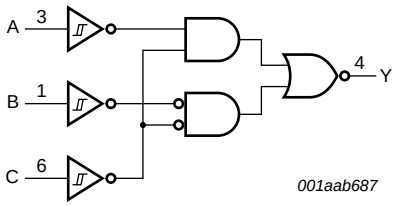


Fig 1. Logic symbol

6. Pinning information

6.1 Pinning

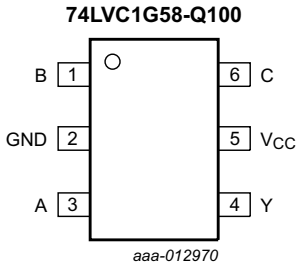


Fig 2. Pin configuration SOT363 and SOT457

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V_{CC}	5	supply voltage
C	6	data input

7. Functional description

Table 4. Function table[1]

Inputs			Output
C	**B**	**A**	**Y**
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	L
H	H	H	L

[1] H = HIGH voltage level; L = LOW voltage level

7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input NAND	see Figure 3
2-input NAND with both inputs inverted	see Figure 6
2-input AND with inverted input	see Figure 4 and 5
2-input NOR with inverted input	see Figure 4 and 5
2-input OR	see Figure 6
2-input OR with both inputs inverted	see Figure 3
2-input XOR	see Figure 7
Buffer	see Figure 8
Inverter	see Figure 9

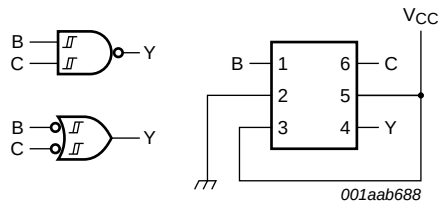


Fig 3. 2-input NAND gate or 2-input OR with both inputs inverted

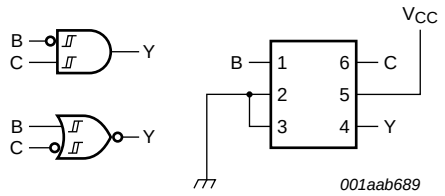


Fig 4. 2-input AND gate with inverted B input or 2-input NOR gate with inverted C input

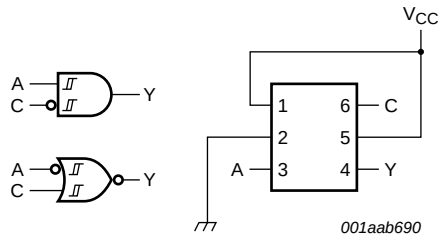


Fig 5. 2-input AND gate with inverted C input or 2-input NOR gate with inverted A input

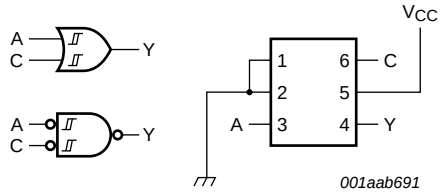


Fig 6. 2-input OR gate or 2-input NAND gate with both inputs inverted

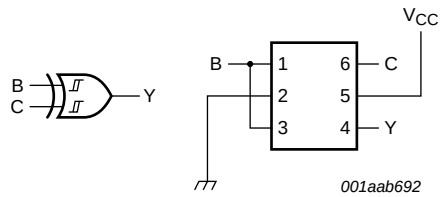


Fig 7. 2-input XOR gate

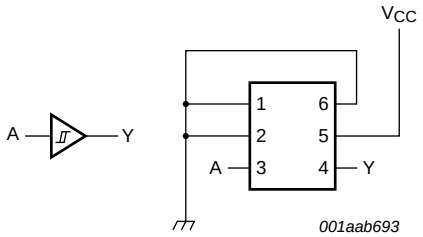


Fig 8. Buffer

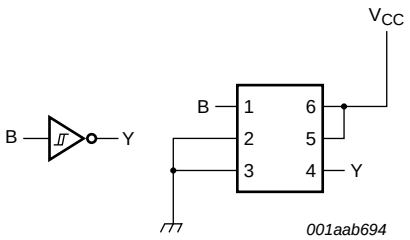


Fig 9. Inverter

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		−50	-	mA
V_I	input voltage		[1]	−0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V		-	±50	mA
V_O	output voltage	Active mode	[1][2]	−0.5	+6.5	V
		Power-down mode	[1][2]	−0.5	+6.5	V
I_O	output current	V_O = 0 V to V_{CC}		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			−100	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C	[3]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	Active mode	0	-	V_{CC}	V
		Power-down mode; V_{CC} = 0 V	0	-	5.5	V
T_{amb}	ambient temperature		−40	-	+125	°C

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T_{amb} = –40 °C to +85 °C						
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 100 μA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.45	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.3	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.4	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.55	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.55	V
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = –100 μA; V_{CC} = 1.65 V to 5.5 V	V_{CC} – 0.1	-	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	1.2	-	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	2.2	-	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.3	-	-	V
		I_O = –32 mA; V_{CC} = 4.5 V	3.8	-	-	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	±0.1	±5	μA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	μA
I_{CC}	supply current	V_I = 5.5 V or GND; V_{CC} = 1.65 V to 5.5 V; I_O = 0 A	-	0.1	10	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC}$ – 0.6 V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	5	500	μA
C_I	input capacitance		-	2.5	-	pF
T_{amb} = –40 °C to +125 °C						
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 100 μA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.7	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.6	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.8	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = –100 μA; V_{CC} = 1.65 V to 5.5 V	V_{CC} – 0.1	-	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	0.95	-	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.7	-	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	1.9	-	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.0	-	-	V
		I_O = –32 mA; V_{CC} = 4.5 V	3.4	-	-	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±100	μA

Table 8. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	-	±200	μA
I_{CC}	supply current	V_I = 5.5 V or GND; V_{CC} = 1.65 V to 5.5 V; I_O = 0 A	-	-	200	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	-	5000	μA

[1] Typical values are measured at maximum V_{CC} and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 11.

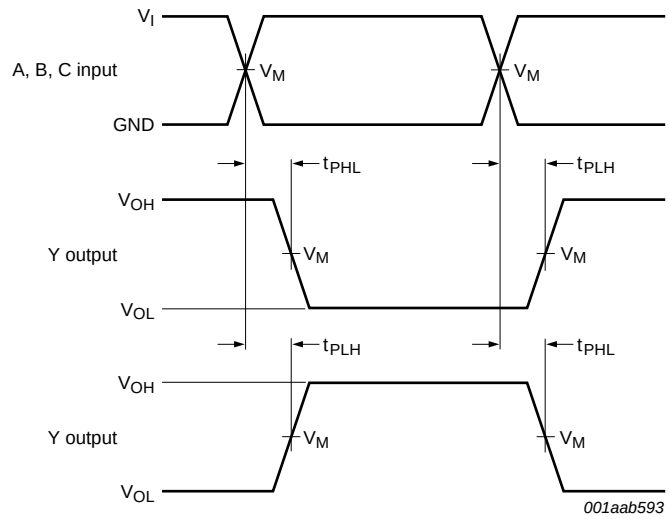
Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	A, B, C to Y; see Figure 10 [2]						
		V_{CC} = 1.65 V to 1.95 V	1.0	6.0	14.4	1.0	18.0	ns
		V_{CC} = 2.3 V to 2.7 V	0.5	3.5	8.3	0.5	10.4	ns
		V_{CC} = 2.7 V	0.5	4.2	8.5	0.5	10.6	ns
		V_{CC} = 3.0 V to 3.6 V	0.5	3.8	6.3	0.5	7.9	ns
		V_{CC} = 4.5 V to 5.5 V	0.5	3.0	5.1	0.5	6.4	ns
C_{PD}	power dissipation capacitance	V_{CC} = 3.3 V; V_I = GND to V_{CC} [3]	-	20	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



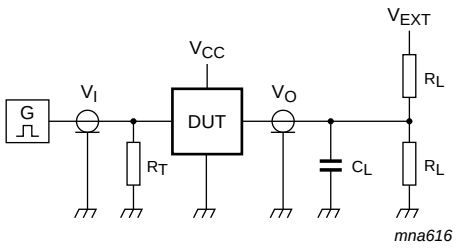
Measurement points are given in Table 10.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 10. Input A, B, C to output Y propagation delay times

Table 10. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 11. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load		V_{EXT}
V_{CC}	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Transfer characteristics

Table 12. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{T+}	positive-going threshold voltage	see Figure 12, Figure 13, Figure 14 and Figure 15						
		V_{CC} = 1.8 V	0.70	1.02	1.20	0.67	1.20	V
		V_{CC} = 2.3 V	1.11	1.42	1.60	1.08	1.60	V
		V_{CC} = 3.0 V	1.50	1.79	2.00	1.47	2.00	V
		V_{CC} = 4.5 V	2.16	2.52	2.74	2.13	2.74	V
		V_{CC} = 5.5 V	2.61	2.99	3.33	2.58	3.33	V
V_{T-}	negative-going threshold voltage	see Figure 12, Figure 13, Figure 14 and Figure 15						
		V_{CC} = 1.8 V	0.30	0.53	0.72	0.30	0.75	V
		V_{CC} = 2.3 V	0.58	0.77	1.00	0.58	1.03	V
		V_{CC} = 3.0 V	0.80	1.04	1.30	0.80	1.33	V
		V_{CC} = 4.5 V	1.21	1.55	1.90	1.21	1.93	V
		V_{CC} = 5.5 V	1.45	1.86	2.29	1.45	2.32	V
V_H	hysteresis voltage	($V_{T+} - V_{T-}$); see Figure 12, Figure 13, Figure 14 and Figure 15						
		V_{CC} = 1.8 V	0.30	0.48	0.62	0.23	0.62	V
		V_{CC} = 2.3 V	0.40	0.64	0.80	0.34	0.80	V
		V_{CC} = 3.0 V	0.50	0.75	1.00	0.44	1.00	V
		V_{CC} = 4.5 V	0.71	0.97	1.20	0.65	1.20	V
		V_{CC} = 5.5 V	0.71	1.13	1.40	0.65	1.40	V

[1] Typical values are measured at T_{amb} = 25 °C.

14. Waveforms transfer characteristics

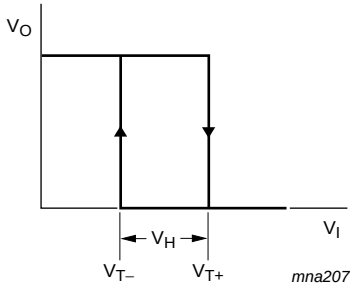
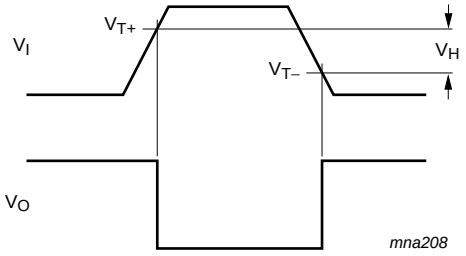


Fig 12. Transfer characteristics



V_{T+} and V_{T-} limits are at 70 % and 20 %.

Fig 13. Definition of V_{T+}, V_{T-} and V_H

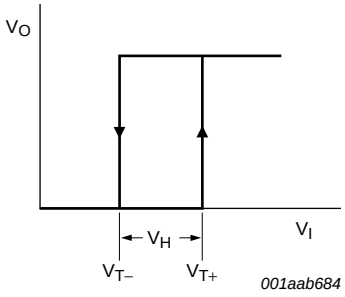
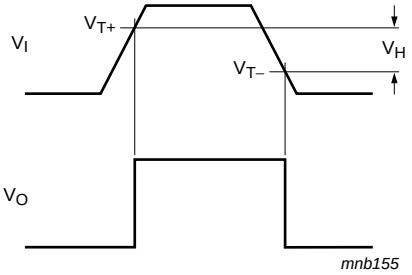


Fig 14. Transfer characteristics



V_{T+} and V_{T-} limits are at 70 % and 20 %.

Fig 15. Definition of V_{T+}, V_{T-} and V_H

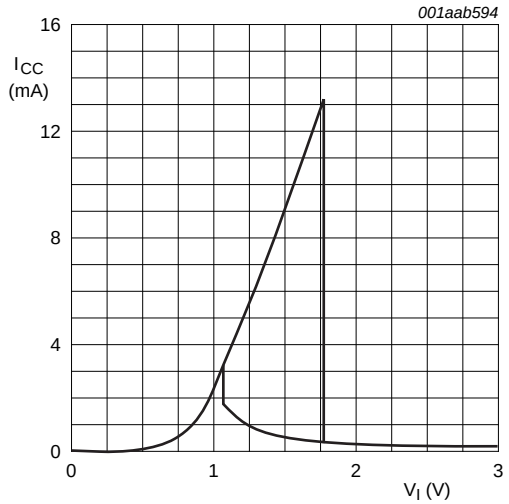
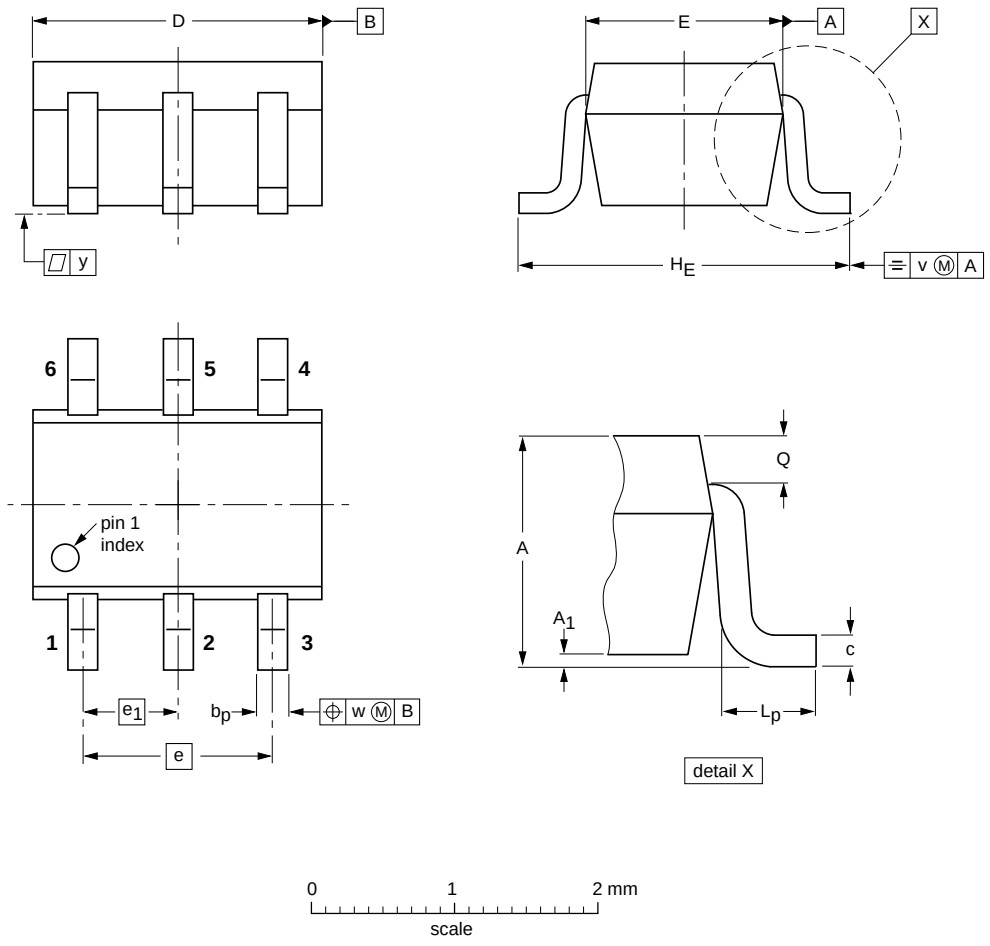


Fig 16. Typical 74LVC1G58-Q100 transfer characteristics; V_{CC} = 3.0 V

15. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



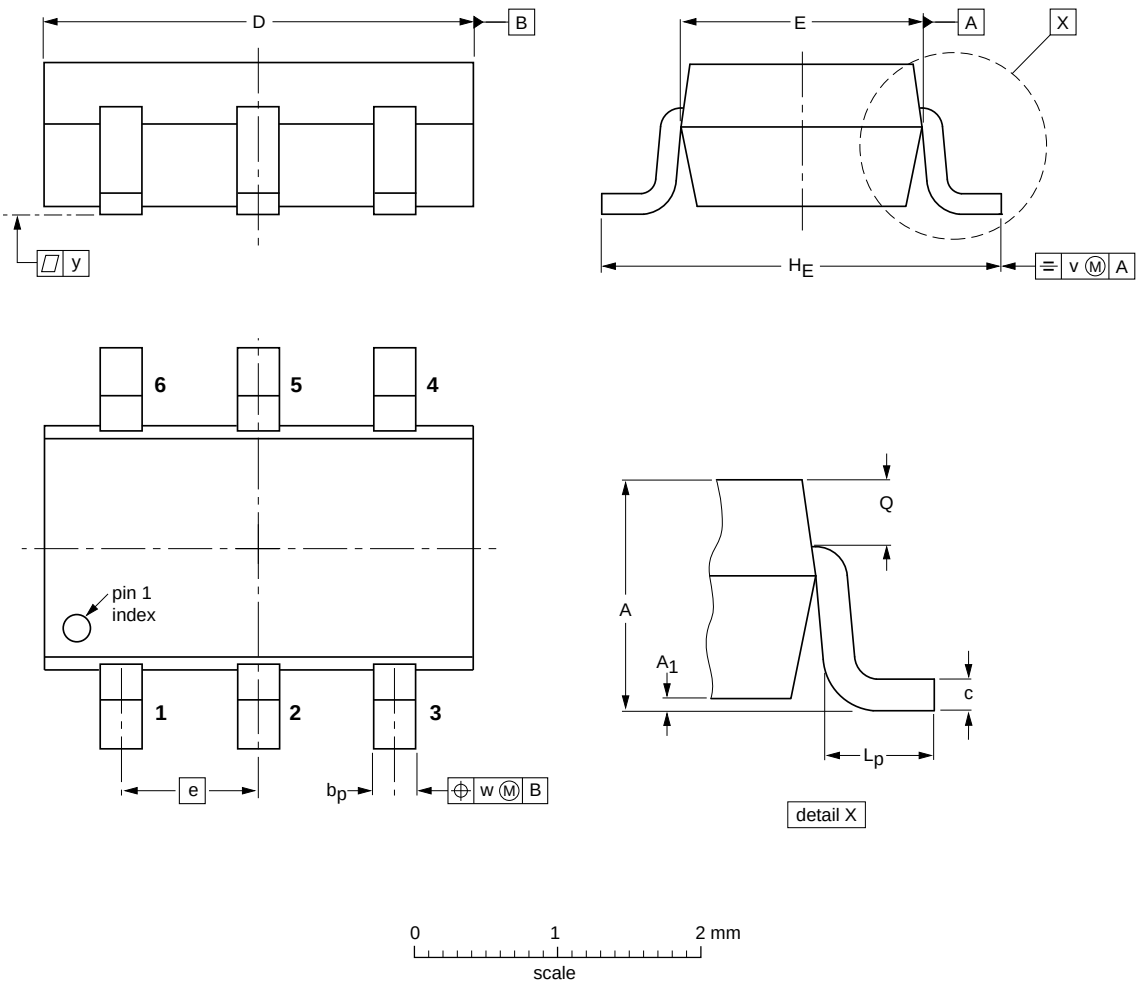
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 17. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads **SOT457**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT457			SC-74			~~05-11-07~~ 06-03-16

Fig 18. Package outline SOT457 (TSOP6)

16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G58_Q100 v.1	20140610	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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20. Contents

1	**General description**	**1**
2	**Features and benefits**	**1**
3	**Ordering information**	**2**
4	**Marking**	**2**
5	**Functional diagram**	**2**
6	**Pinning information**	**2**
6.1	Pinning	2
6.2	Pin description	3
7	**Functional description**	**3**
7.1	Logic configurations	3
8	**Limiting values**	**5**
9	**Recommended operating conditions**	**5**
10	**Static characteristics**	**6**
11	**Dynamic characteristics**	**7**
12	**Waveforms**	**8**
13	**Transfer characteristics**	**10**
14	**Waveforms transfer characteristics**	**10**
15	**Package outline**	**12**
16	**Abbreviations**	**14**
17	**Revision history**	**14**
18	**Legal information**	**15**
18.1	Data sheet status	15
18.2	Definitions	15
18.3	Disclaimers	15
18.4	Trademarks	16
19	**Contact information**	**16**
20	**Contents**	**17**

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